23.11.2026 Monday		12:00	Registration and Coffee / Snacks			
Session 1	90 min	12:30	Welcome Address			
Theory and Materials		12:40	Miller	Wolfram	IKZ Berlin	Numerical calculations of MoS_2 on MoS_2
		13:00	Fatima	Seerat	Jagiellonian University, Poland	First-Principles Investigation of Electronic and Structural Properties of Advanced Materials
		13:20	Leitner	Simon	IKZ Berlin	Synthetic Fluorophlogopite Mica Dielectric Enables Memory Transistors
		13:40	Liu	Shishi	FU Berlin, SupraFAB	Reactivity-Guided Janus Graphene With Asymmetric Interfacial Electrostatics for Tunable Charge Transport
		14:00	Session ends			
		30 min. Coffee Break				
Session 2	80 min	14:30	Beschoten	Bernd	2Phys, RWTH	Benchmarking the integration of hexagonal boron nitride crystals and thin films into graphene-based van der Waals heterostructures
Materials and Processing		14:50	Dulisch	Hubert	2Phys, RWTH	How to build high performance cryogenic FETs and quantum dot devices from bilayer graphene?
		15:10	Kumar	Avinash	AMO, Aachen	2D materials integrated on waveguides for nonlinear optics
		15:30	Kaiser	Stefan	CST, RWTH Aachen	Impact of Al_2O_3 passivation on FETs based on MOCVD monolayer MoS_2
		15:50	Session ends			
		30 min. Coffee Break				
Session 3	80 min.	16:20	Matkovic	Aleksandar	IKZ Berlin	Vapor liquid solid growth of MoS_2 ribbon networks on mica
Deposition I		16:40	Mauder	Christof	AIXTRON	Controlled Synthesis of 2D Materials for Integration into Advanced Semiconductor Process Flows
		17:00	Wang	Ye	TU/e, The Netherlands	Interfacial mechanochemistry of 2D quantum materials growth
		17:20	Tang	Haonan	FZ Jülich	Growth Study of Hexagonal Boron Nitride (h-BN)/Graphene Heterostructures on c-Plane Sapphire by MOCVD
		17:40	Session ends			
Dinner		18:30	Café Anvers (anvers-cafe.de)			
24.11.2026 Tuesday		08:30	Registration and Coffee			
Session 4	80 min	09:00	Bazta	Otman	UDE, Duisburg	Rapid, vacuum-free spray-ILGAR growth of In–Se nanofilms
Deposition II		09:20	Pezhumkat	Jasnamol	Uni Göttingen	Growth of Intercalated Chromium Telluride vdW Thin Tilms with Tuneable Ferromagnetism and Transport Properties.
		09:40	Mohammac	Maryam	AMO, Aachen	Growth of Layered Metal-Organic Chalcogenides (MOCs)
		10:00	Tang	Songyao	CST, RWTH	MOCVD and Transistor Performance of MoS_2/WSe_2 Heterostructures
		10:20	Session ends			
		30 min. Coffee Break				
Session 5	110 min	10:50	Wang	Yibing	CST, RWTH	Water-Assisted MOCVD of Multilayer WSe_2: Characterization and FET Performance
Deposition III		11:10	Lensker	Eric	AIXTRON	Low-Temperature MOCVD Growth of MoS_2 on Si/SiO_2 Substrates using Cl_2 Coflow
		11:30	Deußen	Tobias	CST, RWTH	Selective area growth of TMDCs via MOCVD
		11:50	Ding	Yingfang	CST, RWTH	Tailoring growth and optical properties of MOCVD WS_2 on conductive 4H-SiC substrates
		12:10	Wrap-up, Discussion, Good Bye			
		12:40	Workshop ends			